



**8th ESA Round Table on Micro and Nano Technologies for Space Applications**  
*15 – 19 October 2012*

## **Section 3 – RF MEMS**

**12x12 Switch Matrix**

**Unit based on DPDT MEMS micro-switches in  
LTCC hermetic package**

**THALES**

**INTERNAL THALES ALENIA SPACE**

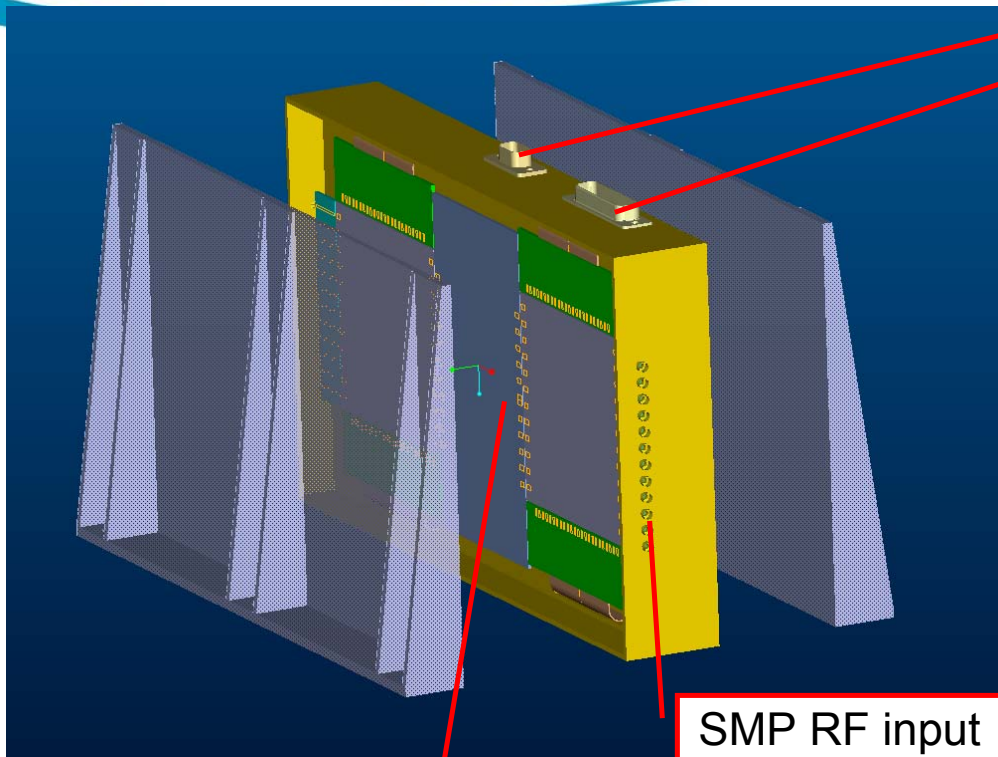
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**The present work has been developed under ESA contract Nr.14628/NL/CK by a Consortium composed by researchers of several organizations in Italy, France and Germany, leaded by Thales Alenia Space Italia as a prime contractor**

- Thales Alenia Space Italia
  - Technical Managing, LTCC Packaging, Mechanical Design, Unit Manufacturing and Assembling
- Munich University of Technology – Institute for High-Frequency Engineering
  - Design of the Switch matrix (simulation and layout)
- Università degli Studi di Perugia – Electronics Engineering Dpt.
  - Design of the MEMS DPDT switches (simulation and layout)
- Fondazione Ugo Kessler Trento Italia
  - Fabrication of the MEMS DPDT switches
- Thales Alenia Space France Toulouse
  - Reliability Assessment
- Consiglio Nazionale delle Ricerche (CNR) – Istituto per la Microelettronica e Microsistemi
  - Switch Matrix Unit Test

## Manufacturing and testing of an Engineering Model (EM) unit of the 12x12 switch matrix

- The switch matrix is housed in an aluminum box having RF coax and DC connectors as an electrical interface
- The MEMS switches inside (DPDT) are driven by a control circuit housed in the unit box, which accepts the memory load (ML-16) configuration commands
- The unit box is also prepared for housing a DC-DC converter circuit suitable to power the control circuit and generate from the primary bus voltage the high voltage needed for the MEMS switches to close their membrane contact (+60V)
- The unit is being designed according to the flight standards and will be subjected either to electrical or environmental testing (TVAC, random vibration, ect.), in order to prove the flight worthiness of the design

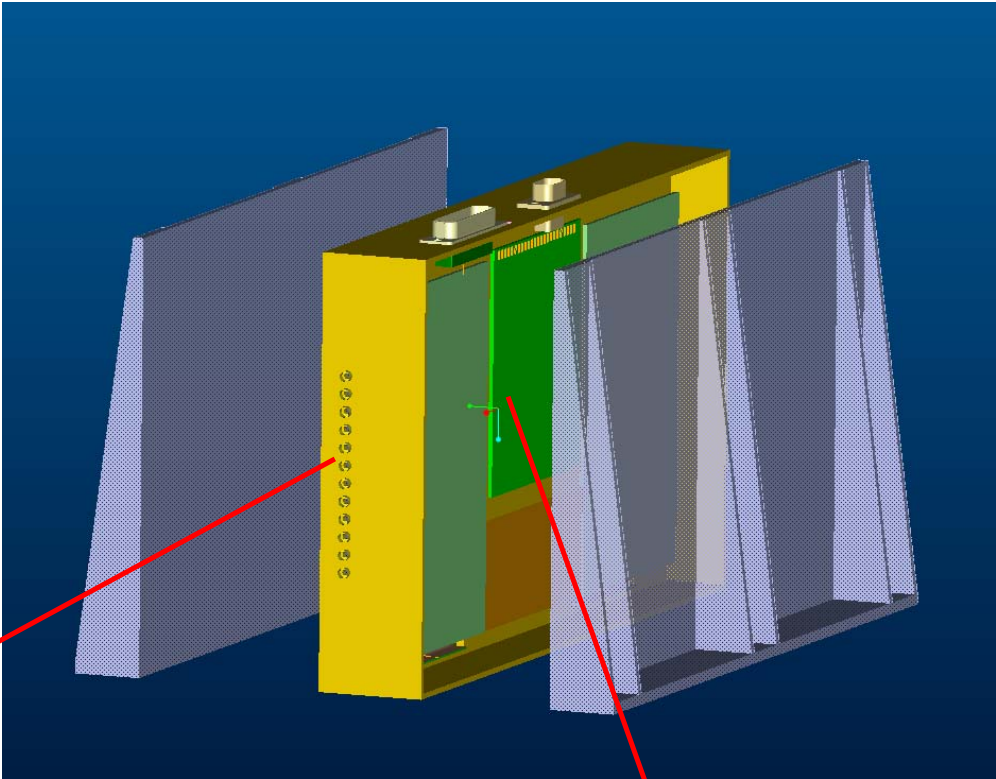


Power and  
Command  
Connectors

SMP RF input  
connectors

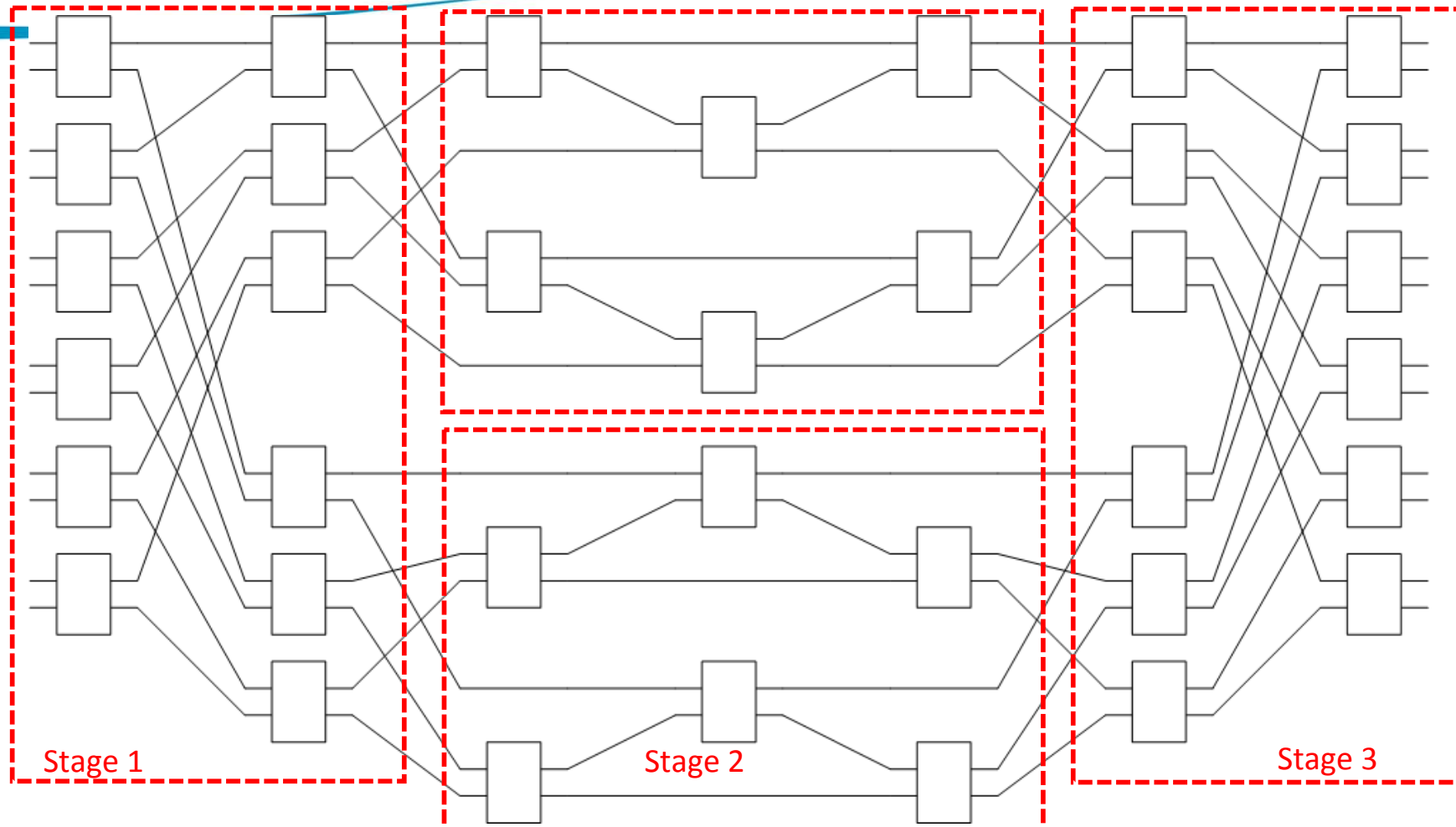
LTCC hybrid  
modules

SMP RF  
output  
connectors



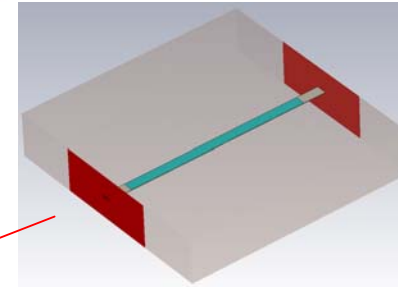
Control and DC-  
DC converter  
boards

Dimensions: 280mm x 160mm x 40mm  
Mass= 1.790Kg

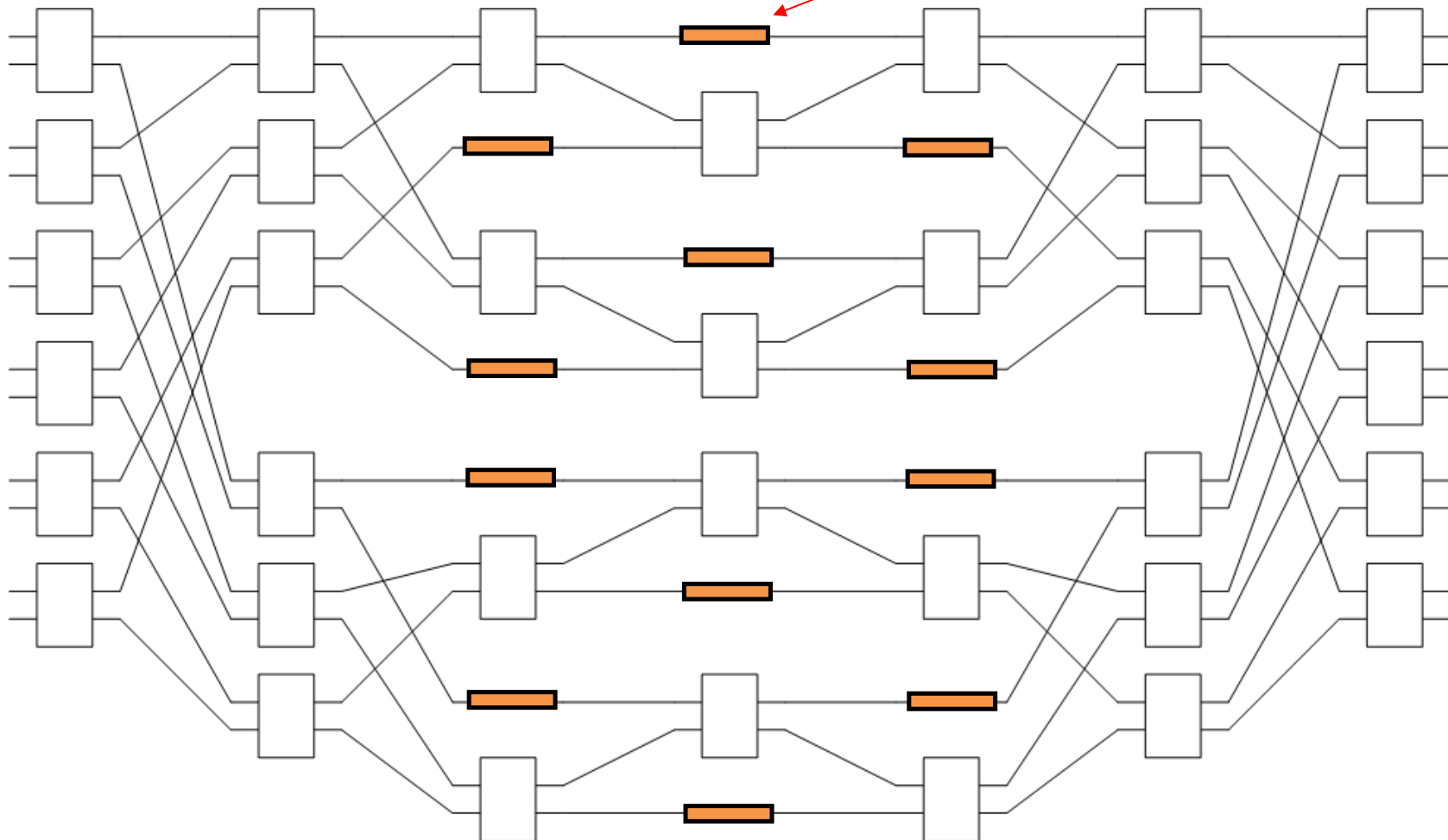


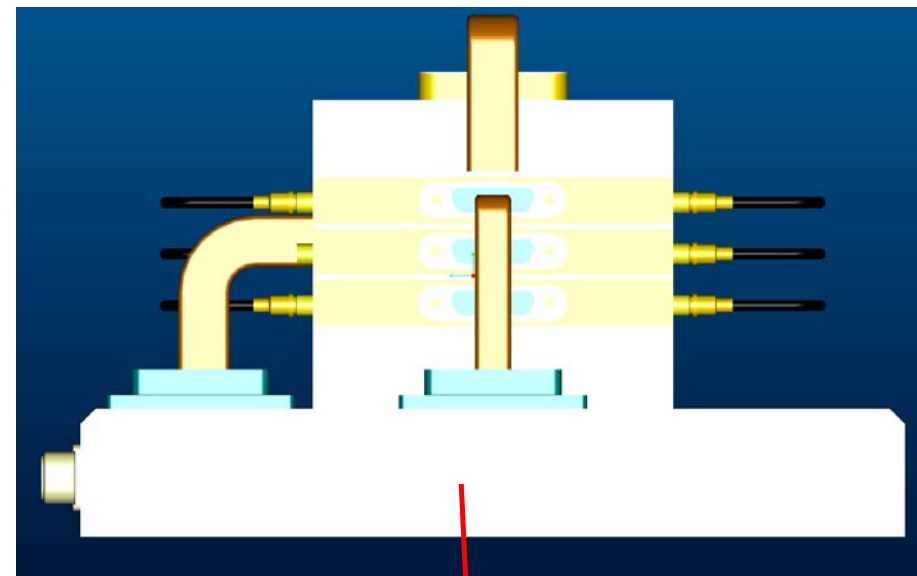
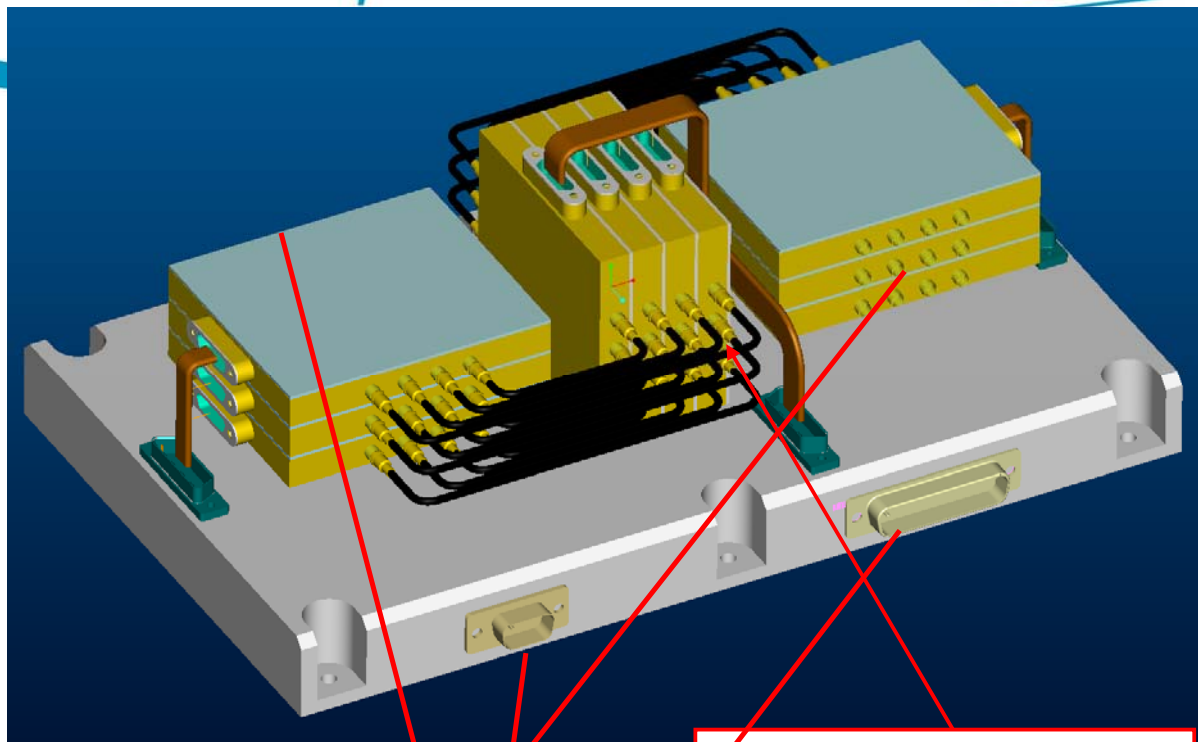
- Basic switching element: DPDT switch (2x2 ring matrix)
- The Planar Benes network can be realized in multilayer LTCC technology
- Four LTCC boards are realized - size 8.5x8.5cm (technology limit)

Resistive lines are inserted to make IL be equal regardless of path assignments.



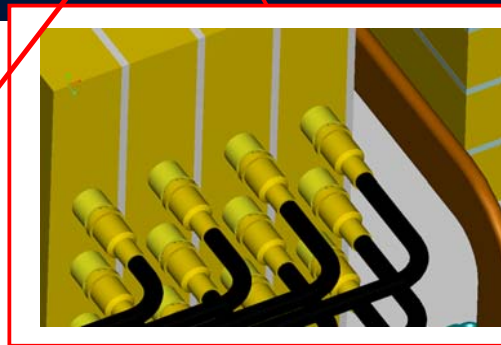
Inserting resistive lines





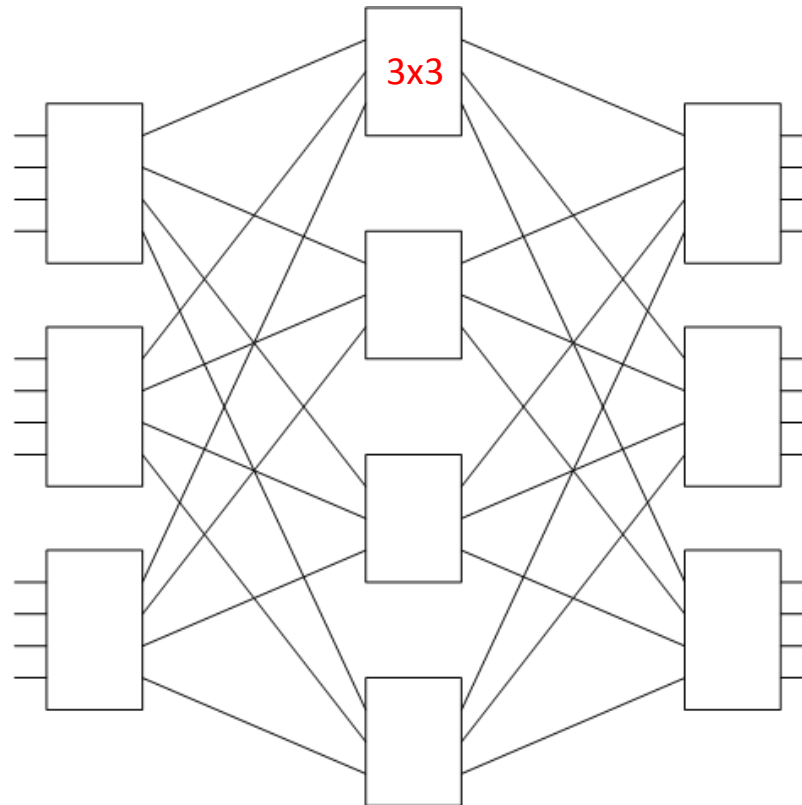
SMP RF  
input/output  
connectors

DC  
connectors



Control and DC-  
DC converter  
boards

Dimensions: 270mm x 160mm x 110mm  
Mass= 3.500Kg





## Planar Benes Topology

### Advantages

- Low Cost
- Easy to assemble
- Reduced Footprint (the unit is mounted on the edge)
- Three hybrid modules only (12x12 matrix)
- High mechanical robustness and compactness

### Drawbacks

- Poorer isolation (but 50dB can be met)
- Not a modular approach

**chosen option!**

## Clos-Benes 3D Configuration

### Advantages

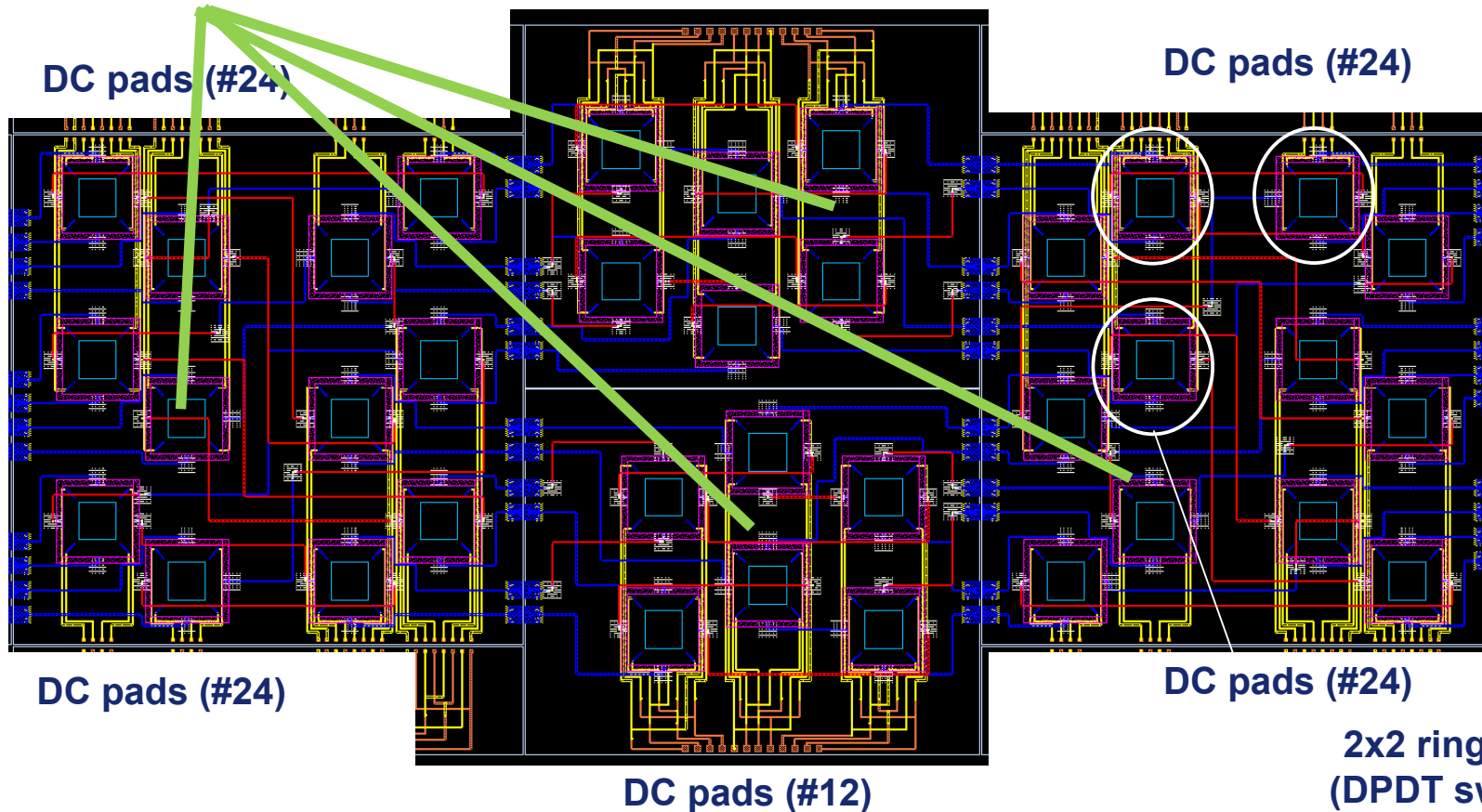
- Modular Approach
- Better isolation

### Drawbacks

- Very high cost (high number of coax cables is required)
- Larger footprint and Mass
- Hard to assemble for either RF or DC wiring
- Mechanically complex

4 LTCC boards (2 identical)

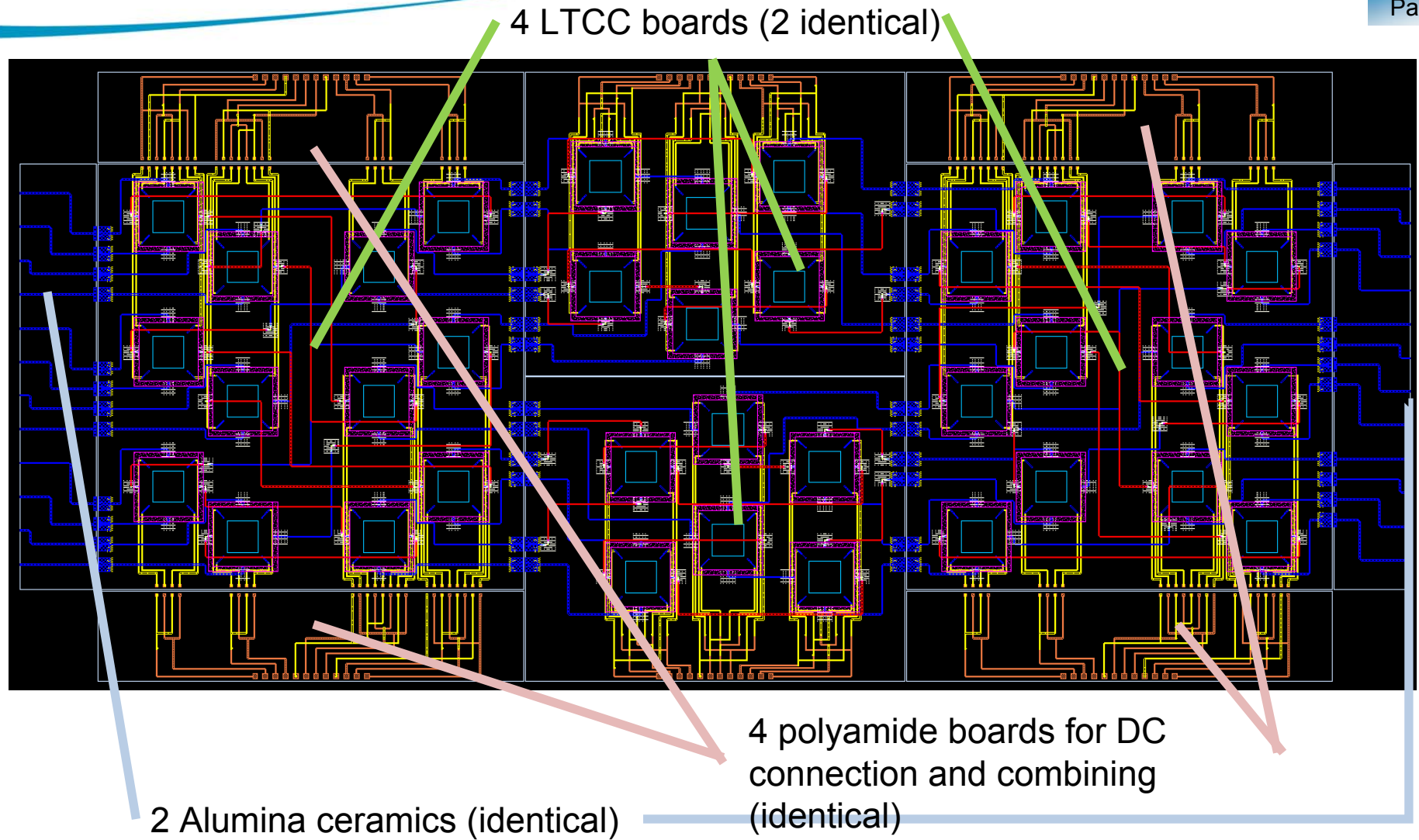
DC pads (#12)

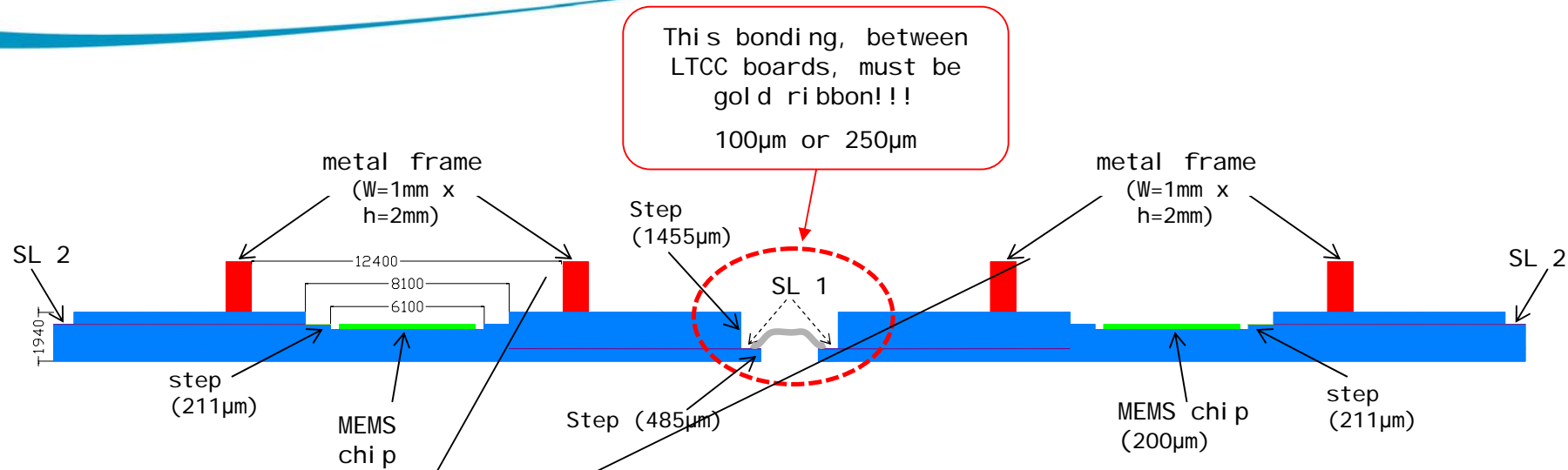


nr.12  
RF I/F  
(CPW)

nr.12  
RF I/F  
(CPW)

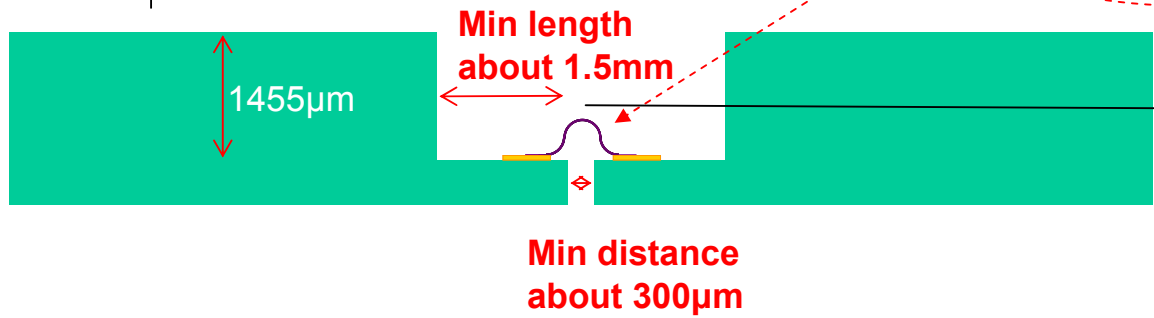
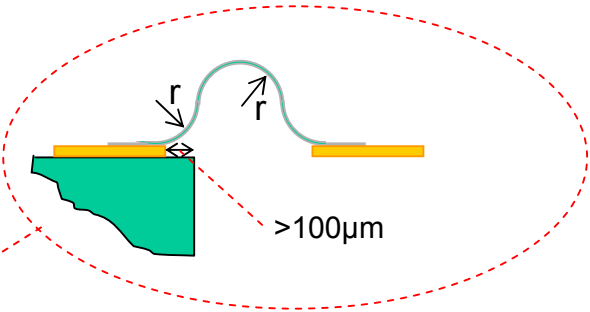
- Four LTCC boards soldered on three carriers made of kovar
- LTCC boards have 14 layers, of which 2 in stripline are used for RF routing and crossing
- Other two layers are used for DC lines used for commanding the switches – in addition such DC lines are resistive to avoid any residual RF radiation that may reduce the isolation performance





This bonding, between LTCC boards, must be gold ribbon!!!  
100µm or 250µm

A metal cap is used to hermetically seal the switches → improve reliability



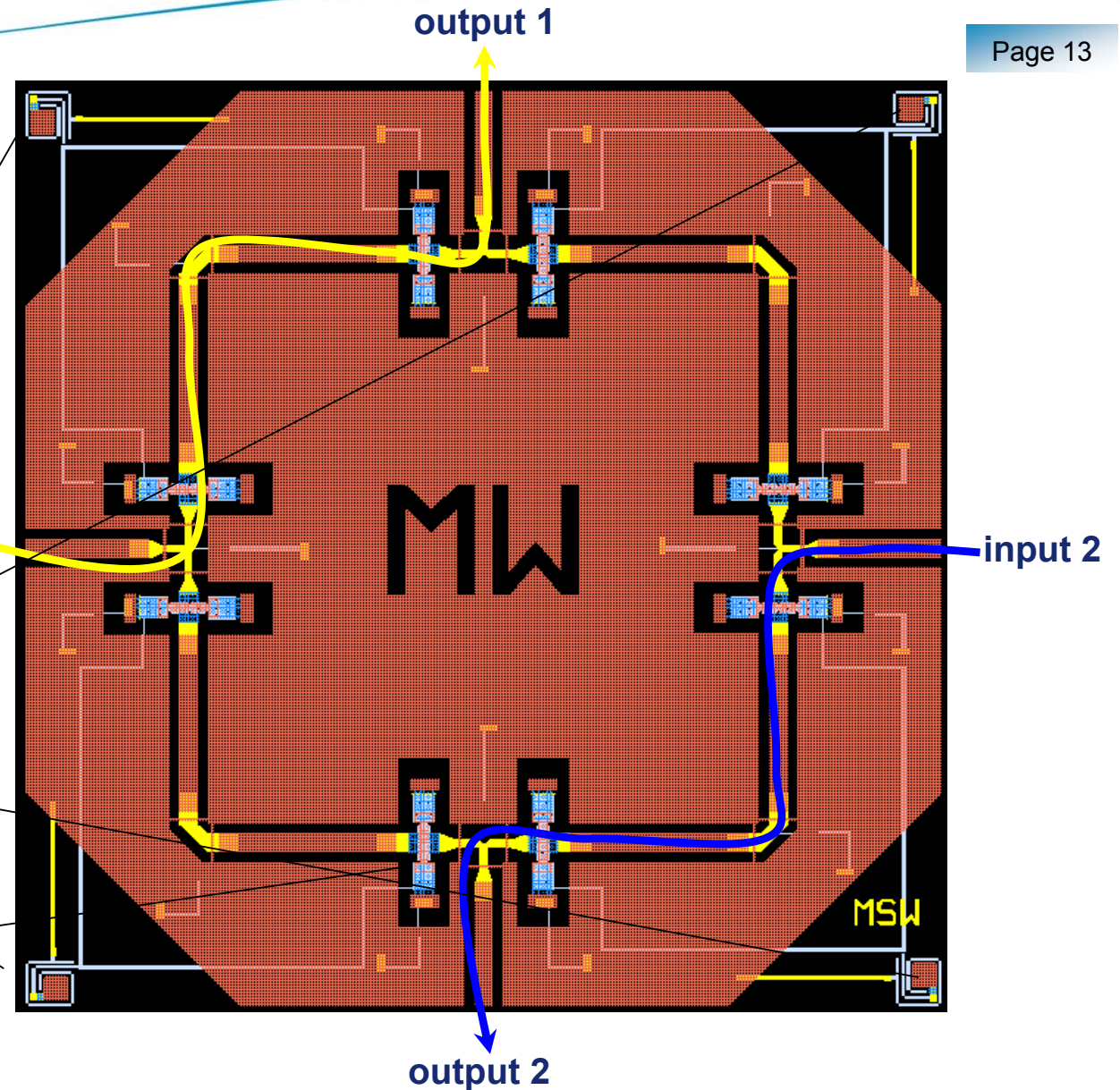
board-to-board connections have been simulated and checked at the assembly phase

## 2x2 non-blocking ring matrix

- Combines two inputs and two outputs by avoiding any crossover
- consists of four CPW SPDT switches
- each SPDT includes two SPST air-bridge membrane series switch (ohmic contact)

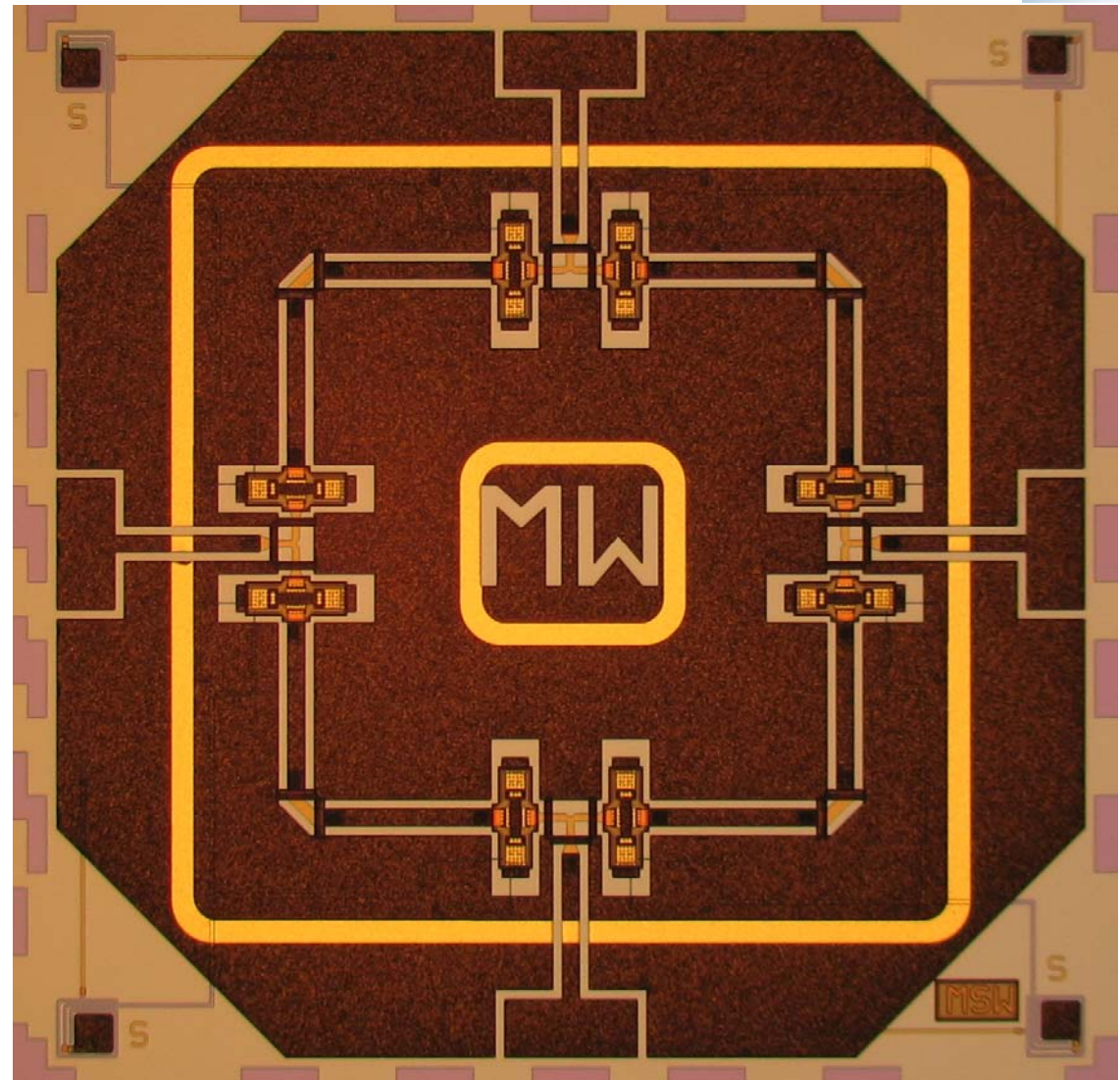
DC pads for switch activation

SPST series switch



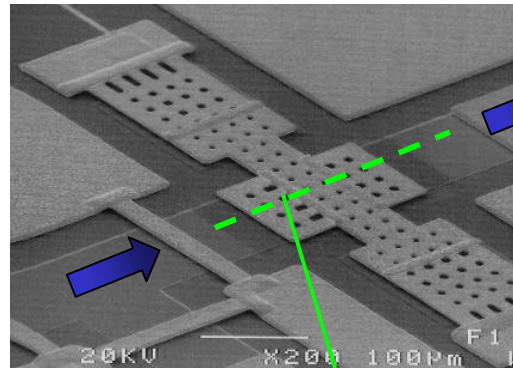
## Fabrication Process

- Substrate: 200um thick high resistive silicon wafer(4 inches)
- 8-mask RF MEMS process developed in FBK
- Electro deposition of two gold layers
- Air bridge realized with no need of planarization steps by using 3um photoresist as a sacrificial layer
- The air-bridges release is done with a modified plasma ashing process, on order to avoid sticking problems
- The bias network uses high-resistivity 0.63um thick poly-silicon layer covered by silicon oxide. This layer is also used for realizing the contact bumps of the ohmic switches
- A third gold layer is deposited for the realization of low resistance metal-to-metal electro-mechanic contacts for the ohmic switches



Picture of the latest version

**Contact-less  
activation  
electrode**

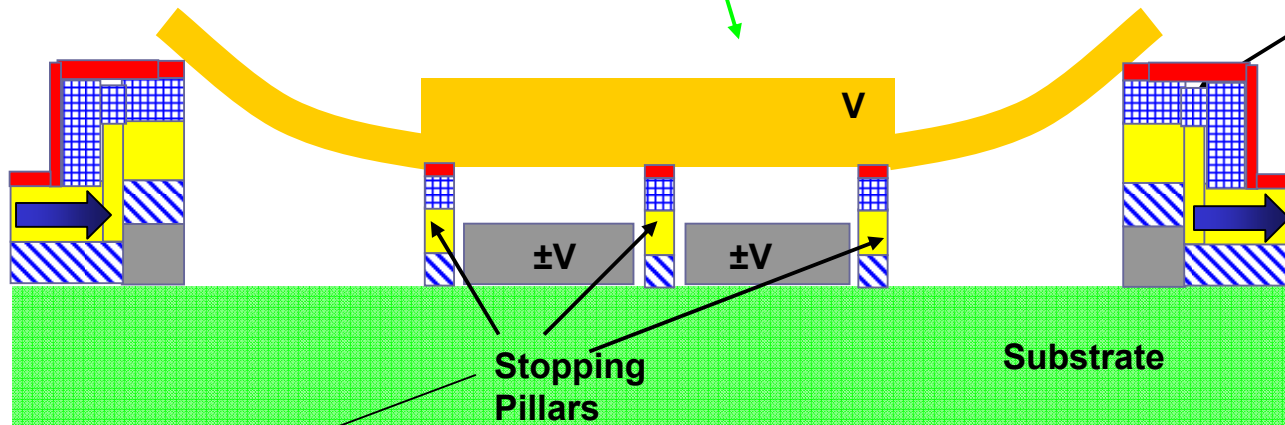


RF line

30 nm thick gold  
100 nm thick LTO dielectric  
630 nm thick Multi metal  
300 nm thick TeOs dielectric  
630/400 nm thick polySi

Substrate

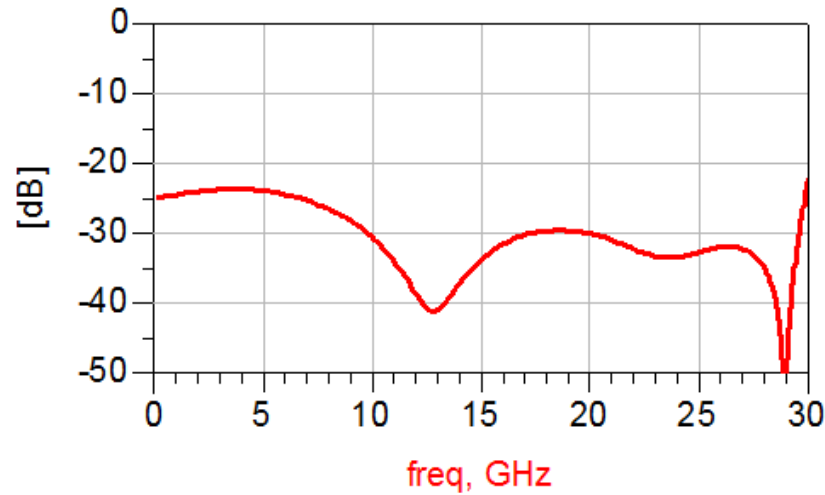
Bumps for  
an  
improved  
Ohmic  
Contact



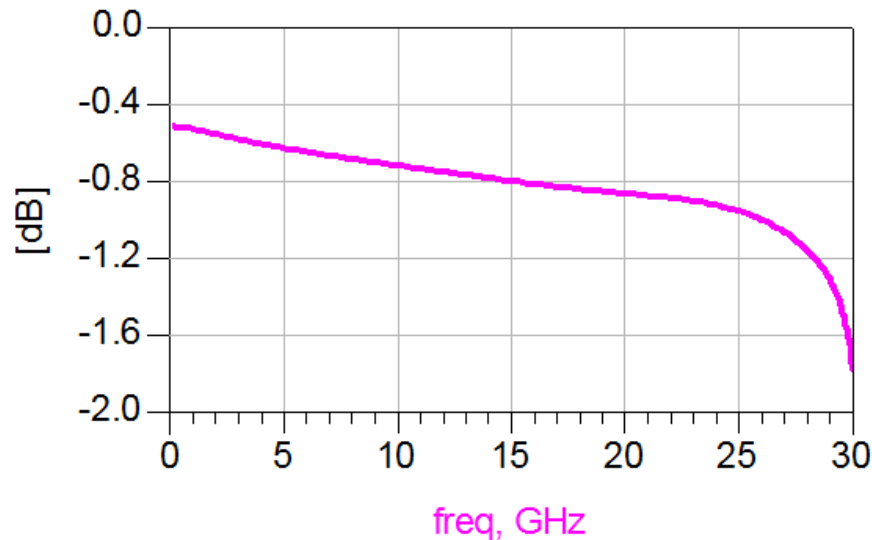
they prevent  
dielectric charging

$\Delta$  stopper-electrode ~ 430/660 nm  
 $\Delta$  stopper-bump ~ 630/400 nm

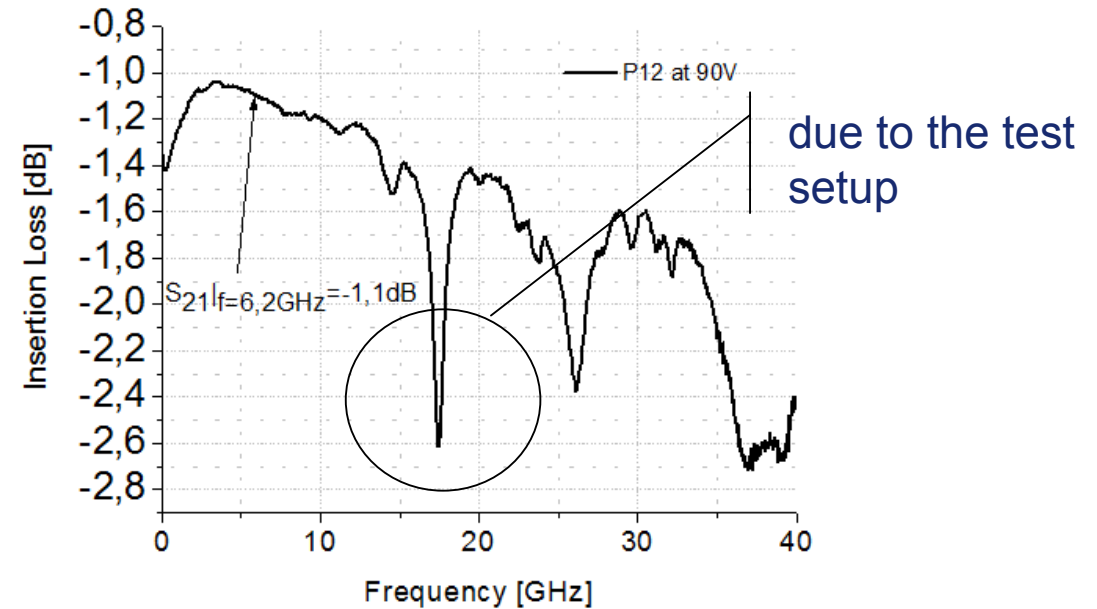
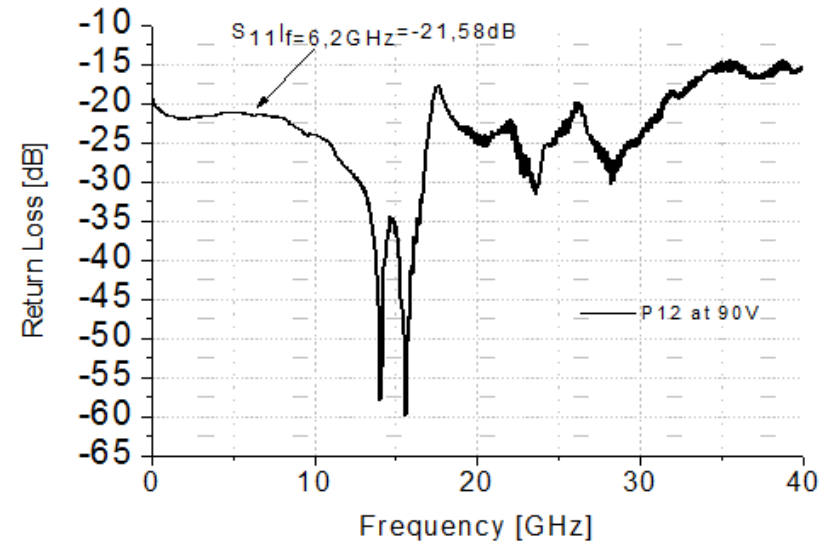
Return Loss



Insertion Loss

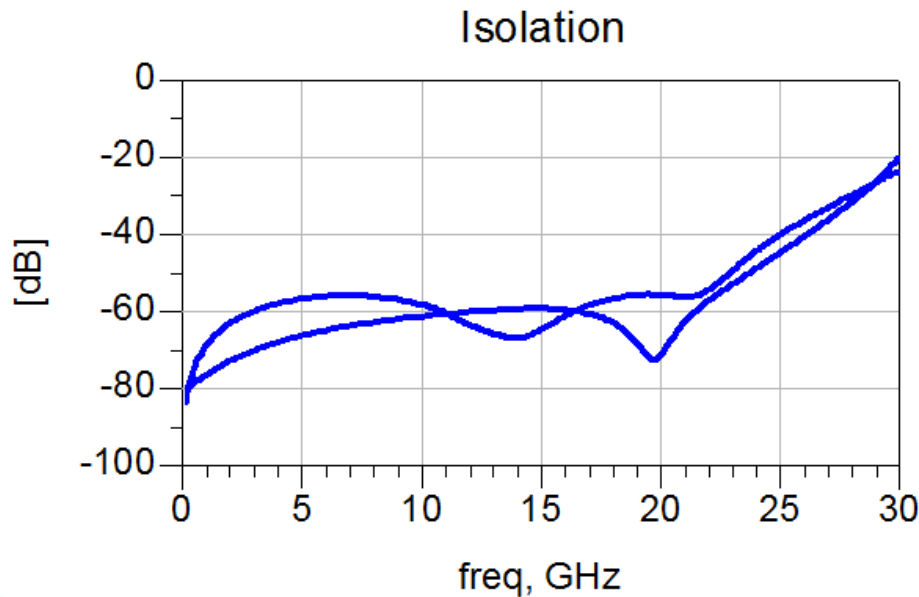


Simulation

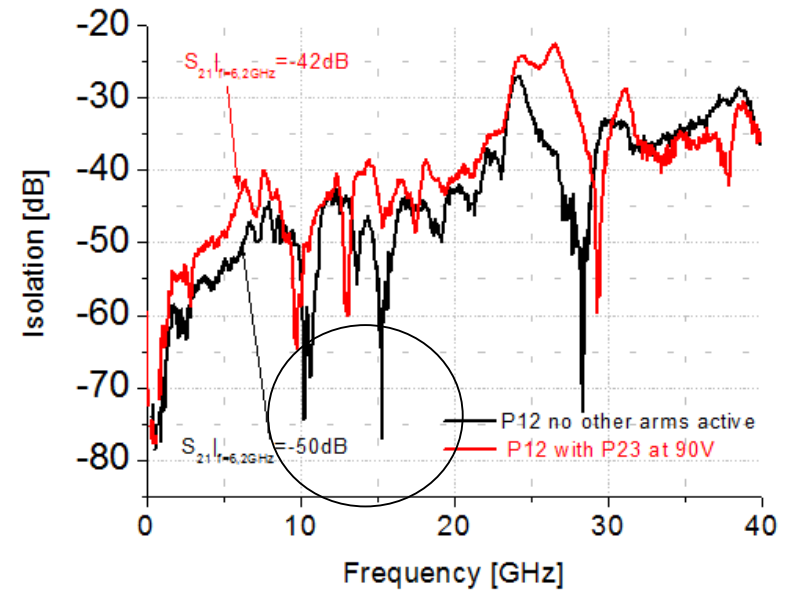


Measurement



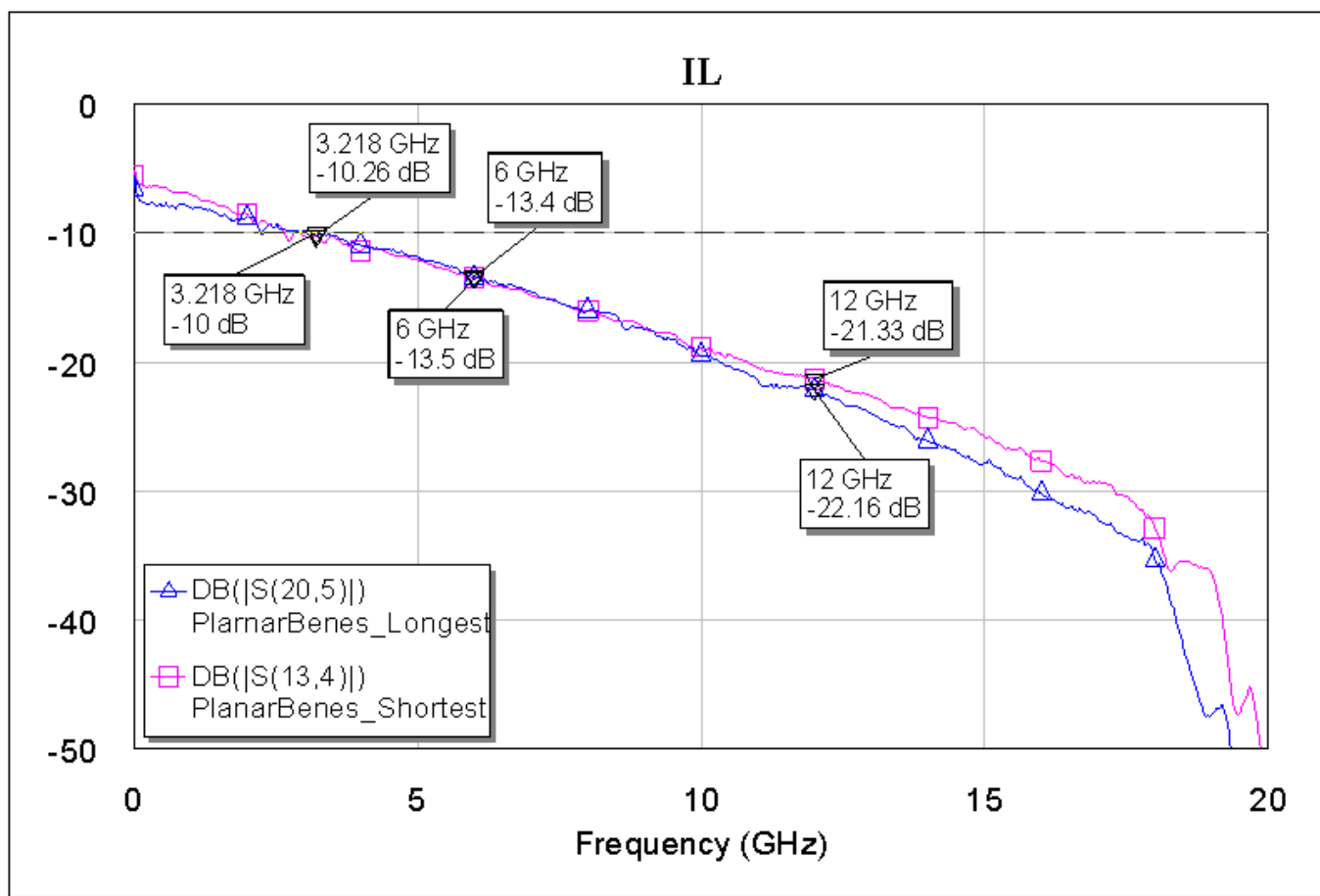


**Simulation**

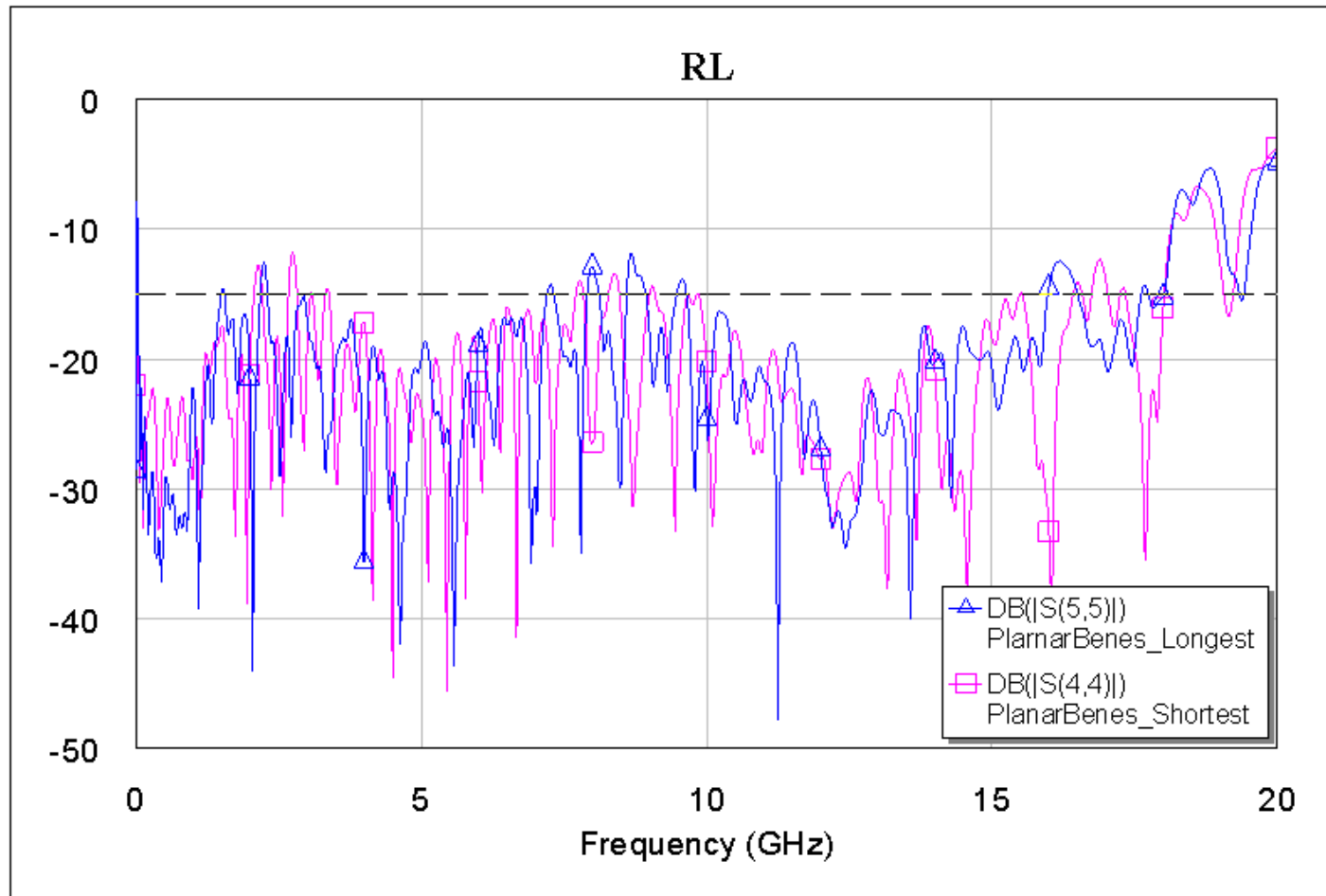


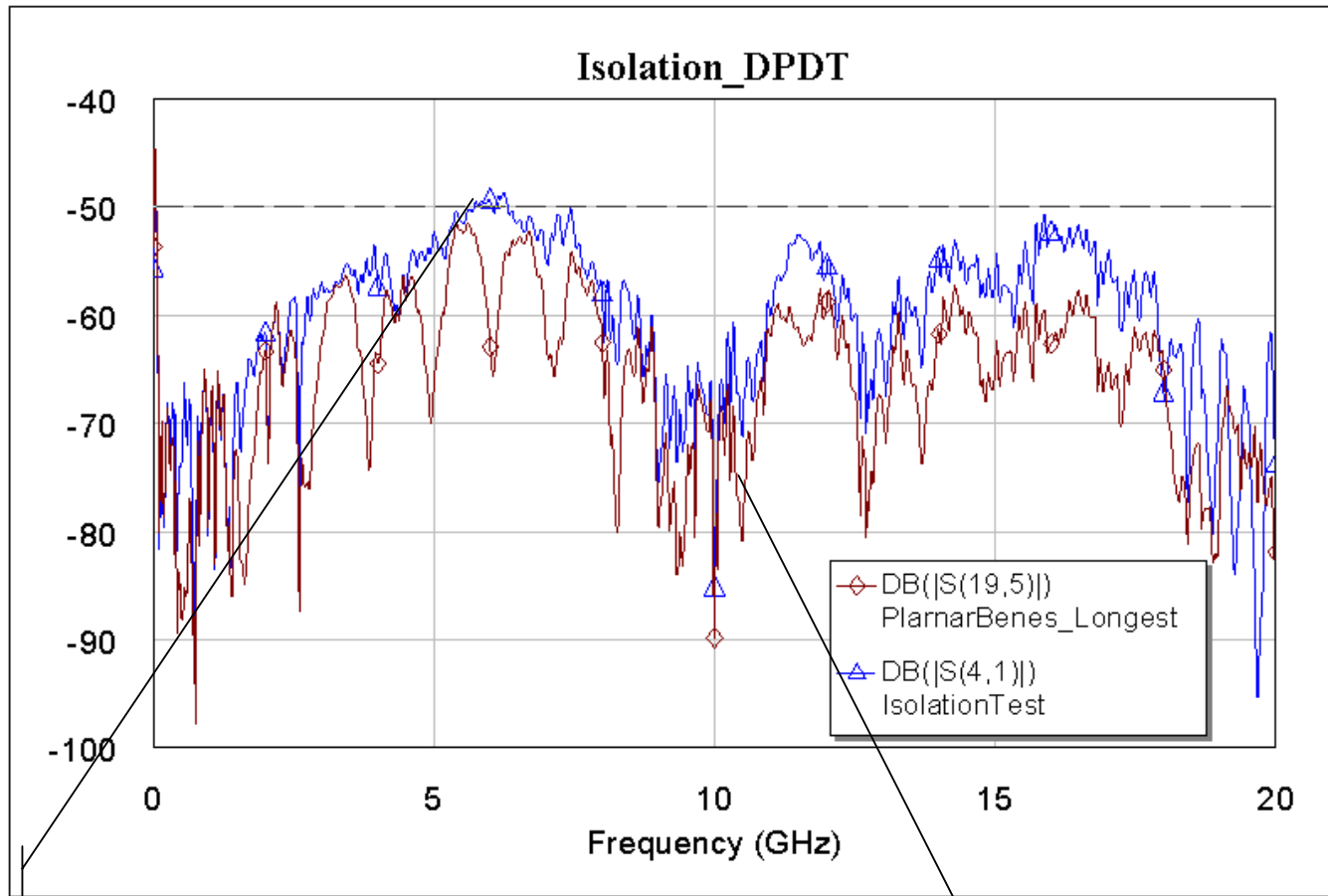
**Measurement**

The Isolation behavior shown an unexpected peak at 6.2GHz (42dB) and resonances, most likely due to the test setup. The real behavior is closer to the simulation.

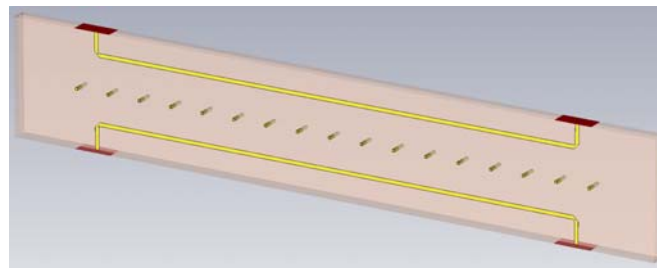


- IL simulation includes: measured DPDT SW performance, Full Wave simulation of : Si-LTCC transition, stripline-to-stripline via, board-to-board transition, board-to-alumina transition, Striplines





Considering coupling either in DPDT switches or between strip lines in the LTCC (blue line)



Considering the coupling in the DPDT switches only (black line)

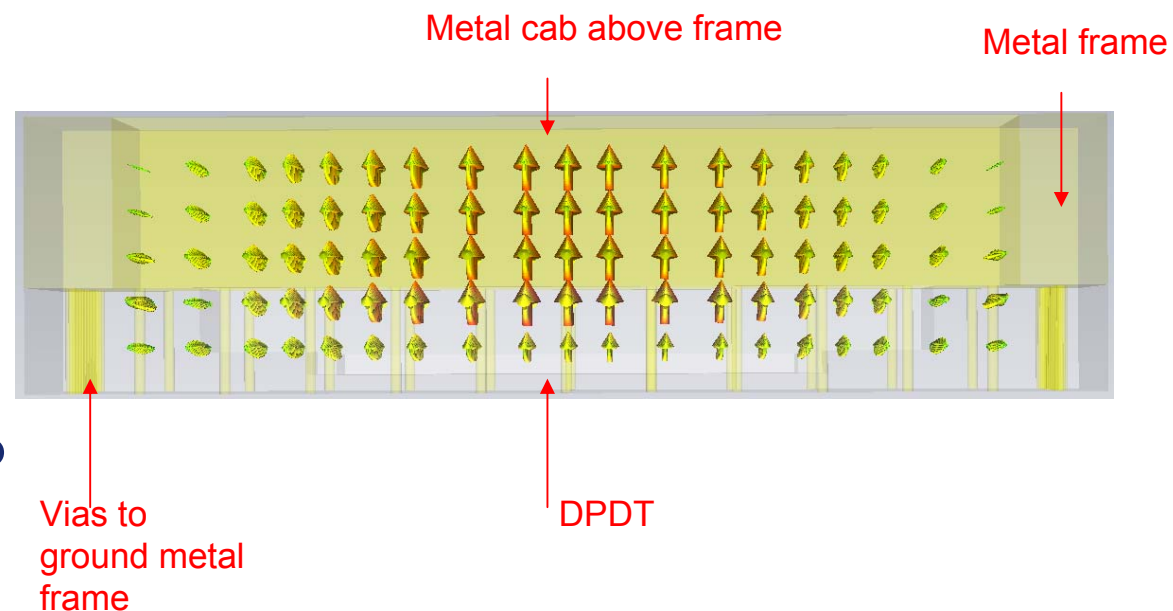
### Return loss and Insertion loss

Bands	RL[dB] (Longest)	IL[dB] (Longest)	RL[dB] (Shortest)	IL[dB] (Shortest)
L(1.2~1.8GHz)	-14.59	-8.955	-17.44	-8.518
S(2.025~2.3GHz)	-12.5	-9.696	-12.75	-9.064
C(3.4~4.2GHz)	-16.89	-11.12	-15.51	-11.13
Ku(10.7~12.75GHz)	-18.69	-23.48	-19.28	-22.37

### Isolation

Bands	Isolation[dB]
L(1.2~1.8GHz)	-65.625
S(2.025~2.3GHz)	-60
C(3.4~4.2GHz)	-56.128
Ku(10.7~12.75GHz)	-52.495

**Note: resonance occurs at 14GHz due to the metal cap, which limits the max freq. of operation**



- The design of a 12x12 Switch Matrix unit based on silicon micro-mechanical switches (RF MEMS) has been presented
- At present, the first design of the silicon MEMS switches has been fabricated and tested showing performances in line with the project specification
- An updated design of the switches has been fabricated to improve the reliability of the membrane contact and their testing is just started
- The switch matrix path routing is realized by using the TASI in-house multilayer LTCC technology
- Simulations and expected performances are available and the LTCC board layers are about to be released for manufacturing
- Expected completion of the Switch Matrix unit fabrication and testing is planned by March 2013

Acknowledgement: Francois Deborgies from ESTEC for his support and suggestions